[Claims]

[Claim 1]
Etchant composition for batch etching treatment of tungsten film and titanium nitride film comprising a nitric acid, water and a sulfuric acid.

[Claim 2]
The etchant composition according to Claim 1, further comprising an aliphatic sulfonic acid.

[Claim 3]
The etchant composition according to Claim 2, wherein the aliphatic sulfonic acid is a methanesulfonic acid.

[Claim 4]
The etchant composition according to any one of Claims 1 to 3 further comprising a phosphoric acid.

[Claim 5]
Method for batch etching of tungsten film and titanium nitride film using the etchant composition comprising a nitric acid, water and at least one selected from the group consisting of a sulfuric acid and an aliphatic sulfonic acid.

[Claim 6]
The method according to claim 5, wherein the aliphatic sulfonic acid is a methanesulfonic acid.

[Claim 7]
The method according to claim 5 or 6 further comprising a phosphoric acid.

[Claim 8]
The method according to any one of claims 5 to 7, wherein the temperature of the etching composition at which the etching is performed is 50 °C or higher.

[Claim 9]
The method according to any one of claims 5 to 8 for generating a pattern having a three-dimensional structure.